

L Number	Hits	Search Text	DB	Time stamp
14	3305	(silicidation or silicide or sin or (silicon near3 nitride)) and (inductor\$1 or (spiral near3 conductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:20
15	353	(silicidation or silicide or sin or (silicon near3 nitride)) SAME (inductor\$1 or (spiral near3 conductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 20:09
16	1547	257/532.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:40
17	486	257/531.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 21:08
18	243	257/534.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:40
19	165	257/535.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:40
20	346	257/621.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:41
21	2543	257/532.ccls. or 257/531.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:41
22	377	(257/532.ccls. or 257/531.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.) and (inductor or (spiral near3 conductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:42
23	328	((257/532.ccls. or 257/531.ccls. or 257/534.ccls. or 257/535.ccls. or 257/621.ccls.) and (inductor or (spiral near3 conductor))) not ((silicidation or silicide or sin or (silicon near3 nitride)) SAME (inductor\$1 or (spiral near3 conductor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:42
24	5	(protrusion or protruding near5 substrate) SAME (inductor\$1 or (spiral near3 conductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 20:10
25	5	((protrusion or protruding) near5 substrate) SAME (inductor\$1 or (spiral near3 conductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 20:10
26	315	257/528.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 21:16

27	113	438/329.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 21:16
-	623	257/532.cccls.	USPAT	2003/11/29 19:40
-	1428	silicidation	USPAT	2002/08/06 21:27
-	6	silicidation and inductor\$1	USPAT	2003/07/25 01:56
-	2	silicide adj prevention	USPAT	2002/08/07 15:00
-	209	257/531.cccls.	USPAT	2003/11/29 19:40
-	31	257/531.cccls. and doped near3 substrate	USPAT	2002/08/07 15:15
-	209	257/531.cccls.	USPAT	2002/08/07 16:50
-	623	257/532.cccls.	USPAT	2002/08/07 16:50
-	111	257/534.cccls.	USPAT	2003/11/29 19:40
-	114	257/535.cccls.	USPAT	2003/11/29 19:40
-	123	257/621.cccls.	USPAT	2002/08/07 16:51
-	0	257/531.cccls. and 257/532.cccls. and 257/534.cccls. and 257/535.cccls. and 257/621.cccls.	USPAT	2002/08/07 16:51
-	1035	257/531.cccls. or 257/532.cccls. or 257/534.cccls. or 257/535.cccls. or 257/621.cccls.	USPAT	2002/08/07 16:52
-	33	(257/531.cccls. or 257/532.cccls. or 257/534.cccls. or 257/535.cccls. or 257/621.cccls.) and doped adj substrate	USPAT	2002/08/07 16:52
-	40	inductor and (doped adj substrate)	USPAT	2002/08/07 17:19
-	410	(silicidation or silicide) and inductor\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/29 19:19
-	261	257/531.cccls.	USPAT	2003/07/25 02:43
-	1489	257/532.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/25 02:44
-	442	257/531.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/25 02:44
-	237	257/534.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/25 02:44
-	153	257/535.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/25 02:44
-	333	257/621.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/07/25 02:44